

Silicon Carbide Diode 31 August 2018

Product data sheet

1. General description

Silicon Carbide Schottky diode in a TO263 (D2PAK) plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- Highly stable switching performance
- High forward surge capability I_{FSM}
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom/Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED/OLED TV
- Motor Drives

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	650	V
I _{F(AV)}	average forward current	$\delta = 0.5$; T _{mb} \leq 106 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3; Fig. 4	-	-	12	A
Static chara	acteristics					
V _F	forward voltage	I _F = 12 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	1.7	V
		I _F = 12 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.8	2.1	V

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected		K A
2	К	cathode[1]		001aaa020
3	А	anode		
mb	К	mounting base; connected to cathode		

[1] It is not possible to connect to pin 2 of the TO263 package.

6. Ordering information

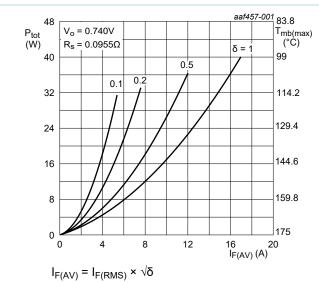
Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
NXPSC12650B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	TO263N				

7. Limiting values

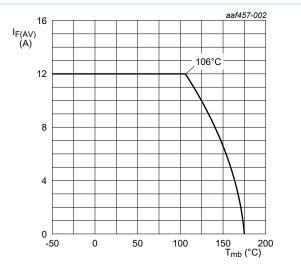
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	650	V
V _{RWM}	crest working reverse voltage		-	650	V
V _R	reverse voltage	DC	-	650	V
I _{F(AV)}	average forward current	$\delta = 0.5$; T _{mb} \leq 106 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3; Fig. 4	-	12	A
I _{FRM}	repetitive peak forward current	δ = 0.5 $\ ;$ t_p = 25 $\mu s;$ square-wave pulse	-	24	A
I _{FSM}	non-repetitive peak	t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse	-	72	А
	forward current	t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse	-	620	A
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-	175	°C





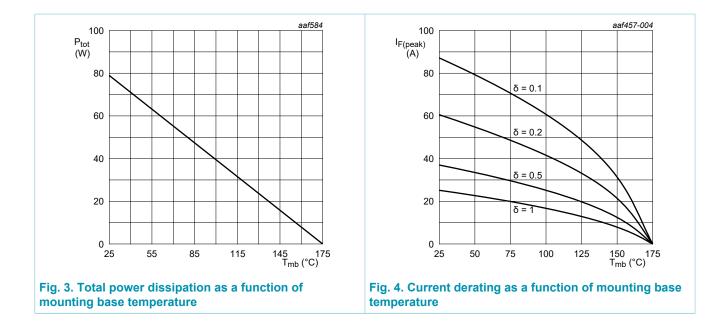




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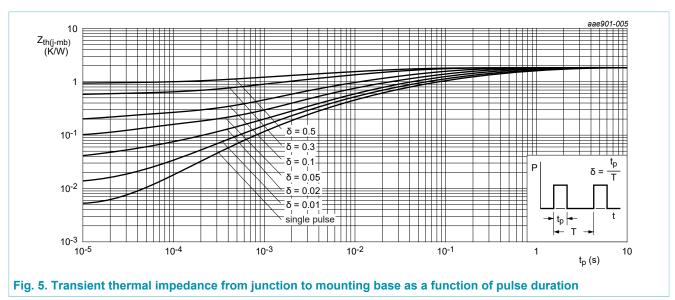


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8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. <u>5</u>	-	-	1.9	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	Device mounted on an FR4 Printed- Circuit Board (PCB)	-	50	-	K/W

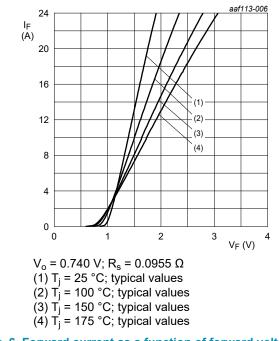


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9. Characteristics

Symbol	Parameter	Conditions	Mi	п Тур	Max	Unit
Static chara	acteristics					,
V _F	forward voltage	I _F = 12 A; T _j = 25 °C; <u>Fig. 6</u>	-	1.5	1.7	V
		I _F = 12 A; T _j = 150 °C; <u>Fig. 6</u>	-	1.8	2.1	V
I _R	reverse current	V _R = 650 V; T _j = 25 °C	-	-	80	μA
		V _R = 650 V; T _j = 150 °C	-	-	320	μA
Dynamic ch	naracteristics	· · · · · · · · · · · · · · · · · · ·				
Q _r	recovered charge	I _F = 12 A; dI _F /dt = 500 A/μs; V _R = 400 V; T _j = 25 °C; <u>Fig. 7</u>	-	18	-	nC
C _d	diode capacitance	f = 1 MHz; V _R = 1 V; T _j = 25 °C	-	380	-	pF
		f = 1 MHz; V _R = 300 V; T _j = 25 °C	-	60	-	pF
		f = 1 MHz; V _R = 600 V; T _i = 25 °C	-	58	-	pF



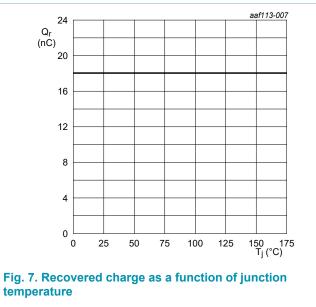


Fig. 6. Forward current as a function of forward voltage; typical values

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10. Package outline

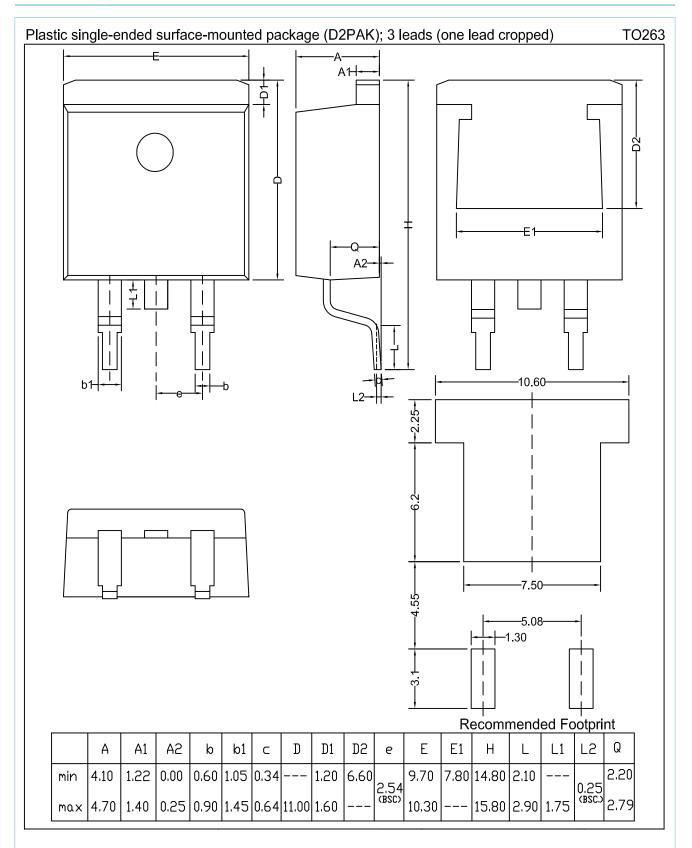


Fig. 8. Package outline D2PAK (TO263N)
NXPSC12650B
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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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NXPSC12650B

12. Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Limiting values	3
8.	Thermal characteristics	5
9.	Characteristics	6
10	Package outline	7
11.	Legal information	8

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